

High Speed Infrared Emitting Diodes, 850 nm, Surface Emitter Technology



DESCRIPTION

As part of the [SurfLight™](#) portfolio, the VSMY1850ITX01 is an infrared, 850 nm emitting diode based on GaAlAs surface emitter chip technology with high radiant intensity, high optical power and high speed, molded in clear, untinted 0805 plastic package for surface mounting (SMD).

FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- AEC-Q101 qualified
- Enhanced operating temperature range: -40 °C to +105 °C
- Peak wavelength: $\lambda_p = 850$ nm
- High reliability
- High radiant power
- High radiant intensity
- High speed
- Angle of half intensity: $\phi = \pm 60^\circ$
- Suitable for high pulse current operation
- 0805 standard surface-mountable package
- Floor life: 72 h, MSL 4, according to J-STD-020
- Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE
GRADE



RoHS
COMPLIANT
HALOGEN
FREE
GREEN
(5-2008)

APPLICATIONS

- Miniature light barrier
- Photointerrupters
- Optical switch
- Emitter source for proximity sensors
- IR touch panels
- IR flash
- IR illumination
- Emitter for automotive applications (e.g. rain sensor)

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
VSMY1850ITX01	10	± 60	850	10

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMY1850ITX01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805

Note

- MOQ: minimum order quantity

**ABSOLUTE MAXIMUM RATINGS** ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100\text{ }\mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100\text{ }\mu\text{s}$	I_{FSM}	1	A
Power dissipation		P_V	190	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	-40 to +105	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-40 to +110	$^{\circ}\text{C}$
Soldering temperature	According to Fig. 7, J-STD-020	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction / ambient	JESD 51	R_{thJA}	270	K/W

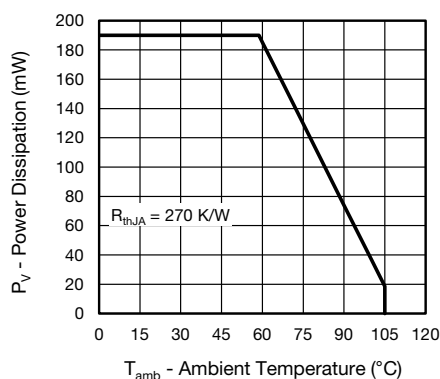


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

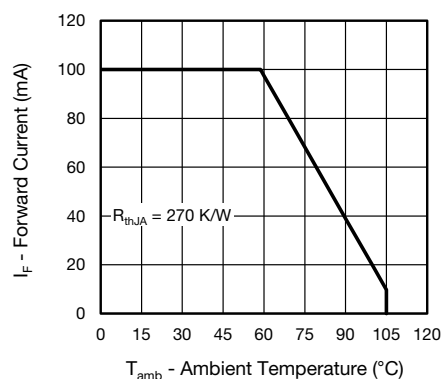


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F	-	1.65	1.9	V
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F	-	2.9	-	V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{VF}	-	-1.4	-	mV/K
	$I_F = 10\text{ mA}$	TK_{VF}	-	-1.18	-	mV/K
Reverse current		I_R	Not designed for reverse operation			μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ mW/cm}^2$	C_J	-	125	v	pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	5	10	15	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e	-	85	-	mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e	-	50	-	mW
Temperature coefficient of radiant power	$I_F = 100\text{ mA}$	TK_{ϕ_e}	-	-0.35	-	%/K
Angle of half intensity		ϕ	-	± 60	-	deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p	840	850	870	nm
Spectral bandwidth	$I_F = 30\text{ mA}$	$\Delta\lambda$	-	30	-	nm
Temperature coefficient of λ_p	$I_F = 30\text{ mA}$	TK_{λ_p}	-	0.25	-	nm/K
Rise time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_r	-	10	-	ns
Fall time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_f	-	10	-	ns
Virtual source diameter		d	-	0.5	-	mm

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

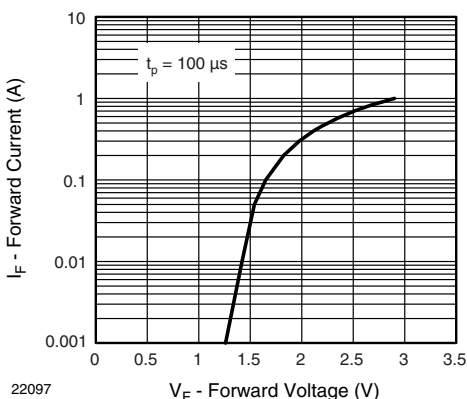


Fig. 3 - Forward Current vs. Forward Voltage

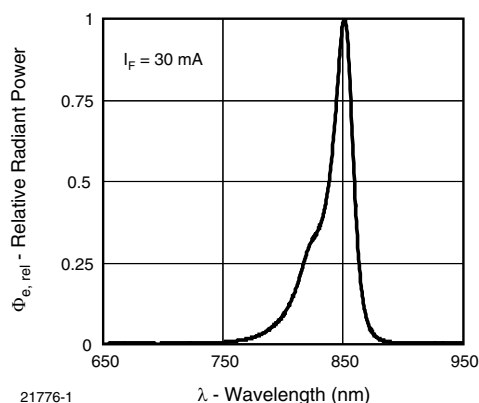


Fig. 5 - Relative Radiant Power vs. Wavelength

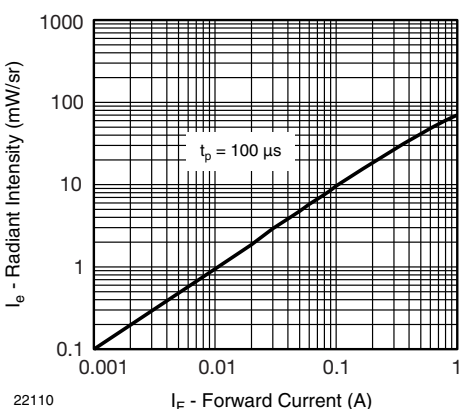


Fig. 4 - Radiant Intensity vs. Forward Current

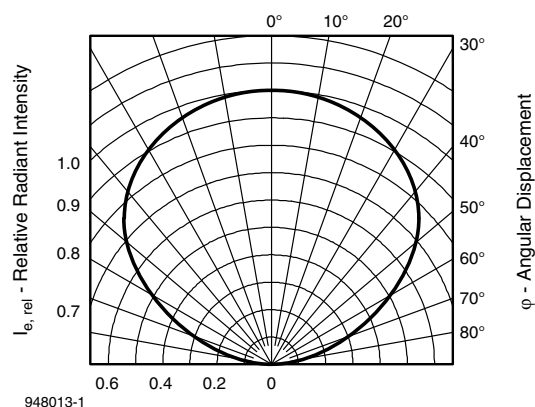


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

REFLOW SOLDER PROFILE

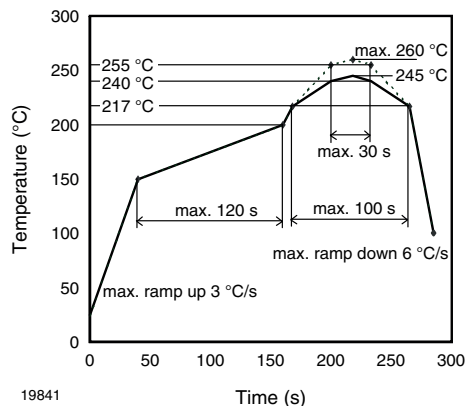


Fig. 7 - Lead (Pb)-free Reflow Solder Profile According to J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 4

Floor life: 72 h

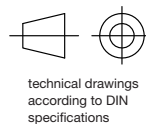
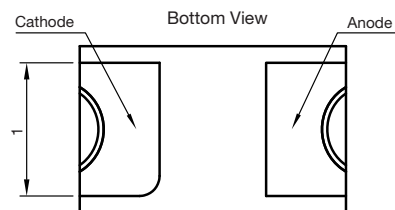
Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at $40\text{ }^{\circ}\text{C}$ (+ 5 °C), RH < 5 %.

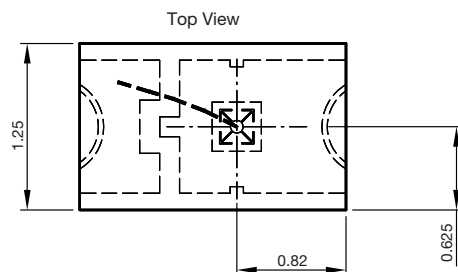
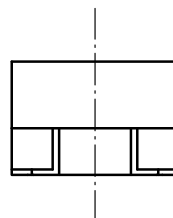
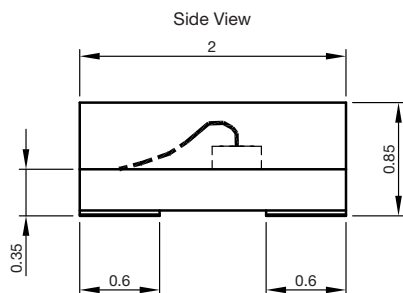


PACKAGE DIMENSIONS in millimeters

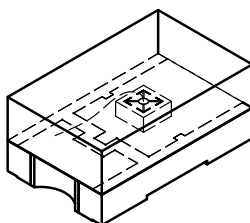
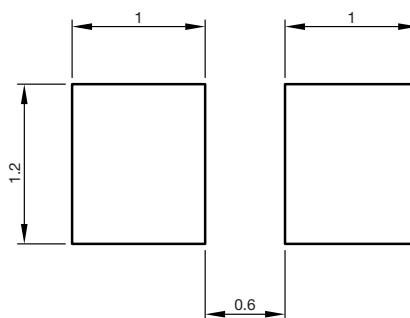


technical drawings
according to DIN
specifications

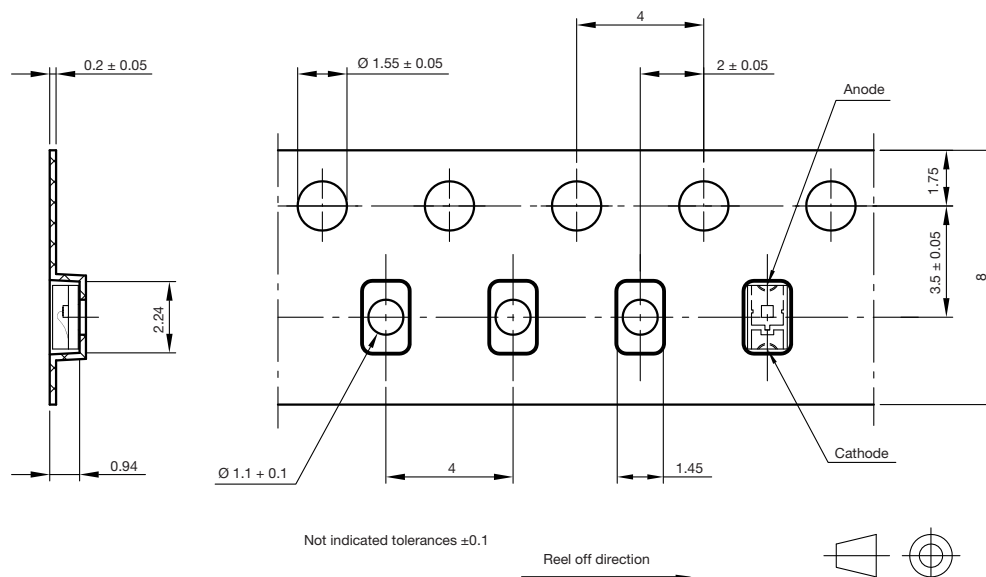
Not indicated tolerances ± 0.1



Recommended solder pad
Footprint



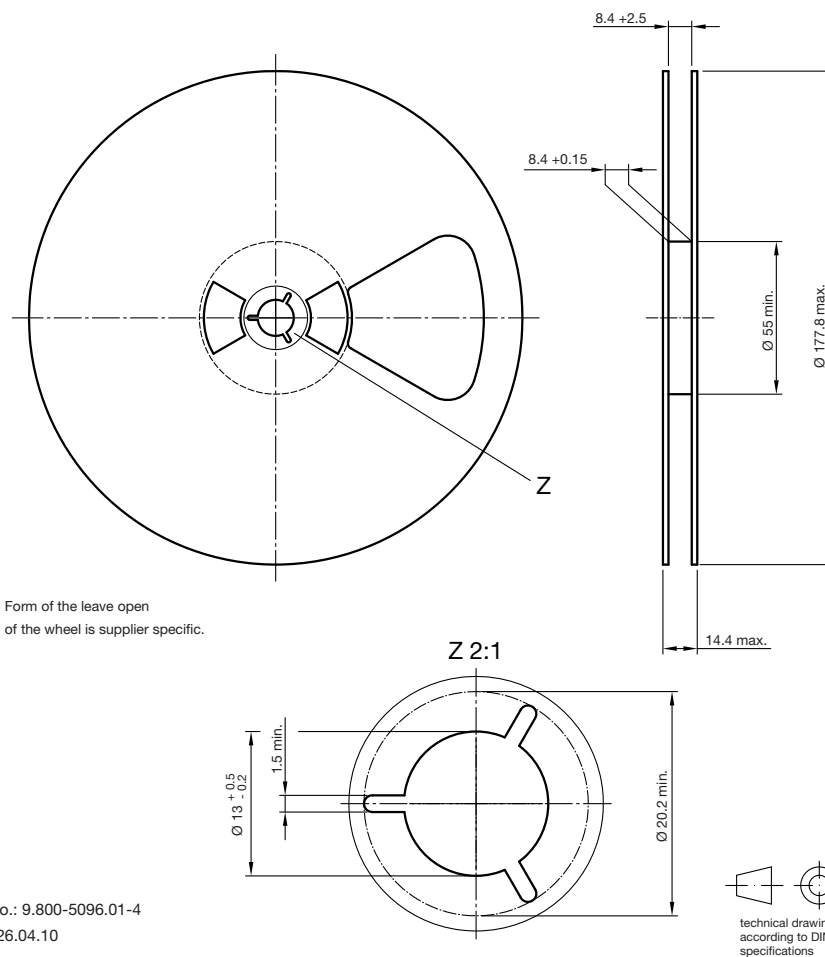
Drawing-No.: 6.541-5083.01-4
Issue: 1; 29.03.10
22111

BLISTER TAPE DIMENSIONS in millimeters

Drawing-No.: 9.700-5352.01-4
Issue: 1; 13.04.10
22112

technical drawings
according to DIN
specifications

REEL DIMENSIONS in millimeters



Drawing-No.: 9.800-5096.01-4
Issue: 2; 26.04.10
20875

technical drawings
according to DIN
specifications



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